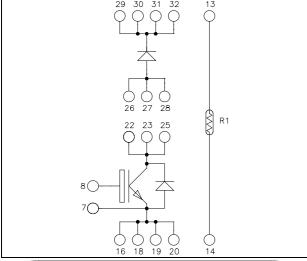
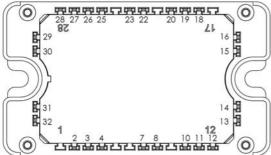


Boost chopper Trench + Field Stop IGBT3 Power Module

 $V_{CES} = 600V$  $I_C = 200A$  @ Tc = 100°C





Pins 29/30/31/32 must be shorted together
Pins 26/27/28/22/23/25 must be shorted together
to achieve a phase leg
Pins 16/18/19/20 must be shorted together

### **Application**

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### **Features**

- Trench + Field Stop IGBT3
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Kelvin emitter for easy drive
- Internal thermistor for temperature monitoring
- AlN substrate for improved thermal performance

#### Benefits

- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

## All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

#### **Absolute maximum ratings**

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Voltage		600	V
I <sub>C</sub> Continuous Collector Current	Continuous Collector Cument	$T_C = 25^{\circ}C$	290	
	Continuous Conector Current	$T_{\rm C} = 100^{\circ}{\rm C}$	200	Α
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	400	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Power Dissipation	$T_C = 25^{\circ}C$	750	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150$ °C	400A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Electrical	Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V <sub>CE(sat)</sub>	Collector Emitter Saturation Voltage	$ \begin{array}{c c} V_{GE} = 15V & T_j = 25^{\circ}C \\ I_C = 200A & T_j = 150^{\circ}C \\ \end{array} $		1.5	1.9	V	
	Collector Emitter Saturation Voltage		$T_j = 150$ °C		1.7		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 2 \text{ mA}$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

**Dynamic Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			12.3		nF	
$C_{oes}$	Output Capacitance				0.8			
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz			0.4			
$Q_{G}$	Gate charge	$V_{GE} = \pm 15V ; V_{CE} = 300V$ $I_{C} = 200A$			2.2		μС	
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C)			115			
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			45		ns	
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 200A$			225			
$T_{\mathrm{f}}$	Fall Time	$R_G = 2\Omega$			55			
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (150°C)			130			
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$			50			
$T_{d(off)} \\$	Turn-off Delay Time	$V_{Bus} = 300V$ $I_C = 200A$			300		ns	
$T_{\mathrm{f}}$	Fall Time	$R_G = 2\Omega$			70			
Eon	Turn on Energy	$V_{GF} = \pm 15V$	$V_{GE} = \pm 15V$ $T_j =$	$T_j = 25^{\circ}C$		1		mJ
Lon	Turn on Energy	$V_{Bus} = 300V$	$T_j = 150$ °C		1.8		1113	
E	T	$I_{\rm C} = 200 {\rm A}$	$T_j = 25$ °C		5.7		Т	
$E_{off}$	Turn off Energy	$R_G = 2\Omega$	$T_j = 150$ °C		7		mJ	
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V ; V_{Bus} = 360V$ $t_p \le 6\mu s ; T_j = 150^{\circ}C$			1000		A	
$R_{thJC}$	Junction to Case Thermal Resistance					0.20	°C/W	

Chopper diode ratings and characteristics

Symbol	Characteristic Test Conditions		Min	Typ	Max	Unit	
$V_{RRM}$	Peak Repetitive Reverse Voltage	_				600	V
$I_{\text{RM}}$	Reverse Leakage Current	$V_{R} = 600V$				250	μΑ
$I_F$	DC Forward Current		$Tc = 80^{\circ}C$		200		Α
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 200A$	$T_j = 25$ °C		1.6	2	V
• •	Blode I of ward Voltage	$V_{GE} = 0V$	$T_j = 150$ °C		1.5		·
$t_{rr}$	Reverse Recovery Time		$T_j = 25$ °C		125		ns
ι <sub>rr</sub>	Reverse Recovery Time	$I_F = 200A$ $V_R = 300V$ $T_j$	$T_j = 150$ °C		220		115
	Reverse Recovery Charge		$T_j = 25$ °C		9		uС
Q <sub>rr</sub>	Reverse Recovery Charge		$T_{\rm j} = 150^{\circ}{\rm C}$		20		μС
Er	Payarsa Pagayary Enargy		$T_j = 25$ °C		2.2		mJ
EI	Reverse Recovery Energy		$T_j = 150$ °C		4.8		1113
$R_{\text{thJC}}$	Junction to Case Thermal Resistance					0.31	°C/W



## Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
$T_{\rm J}$	Operating junction temperature range			-40	175	
$T_{JOP}$	Recommended junction temperature under switching conditions		-40	T <sub>J</sub> max -25	°C	
$T_{STG}$	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight		•		110	g

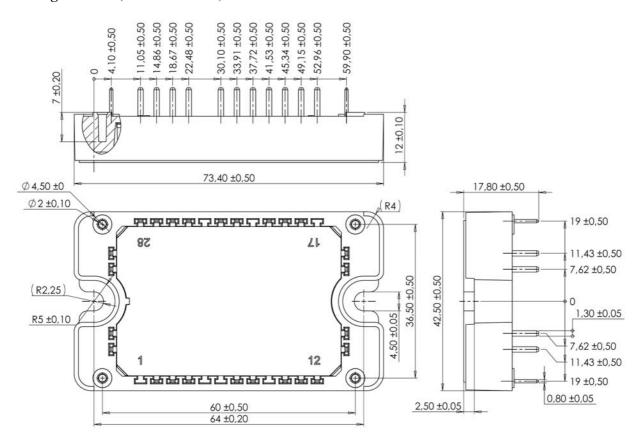
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		$T_C=100$ °C		4		%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]} \quad \text{T: Thermistor temperature}$$

$$R_{T}: \text{ Thermistor value at T}$$

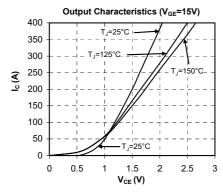
## Package outline (dimensions in mm)

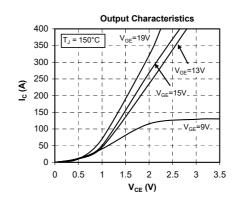


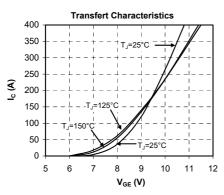
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

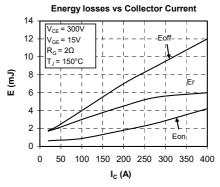


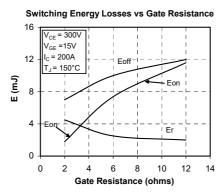
## **Typical Performance Curve**

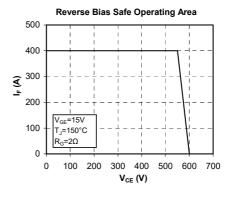


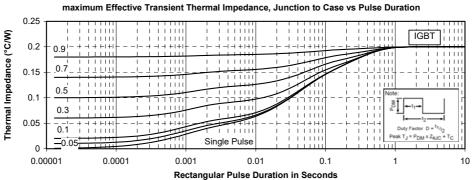




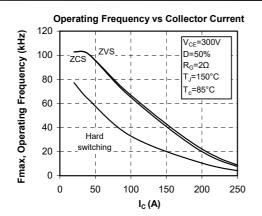


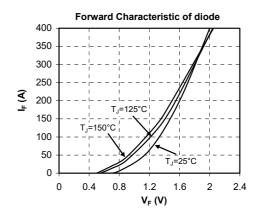


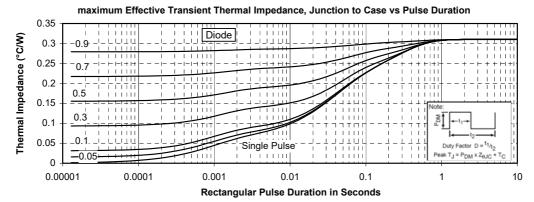












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# APTGT200DA60T3AG – Rev 2 November, 2017



# APTGT200DA60T3AG

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